

Applications

- General Purpose

Product Features

- Frequency Range: 2 – 12 GHz
- Power: 23 dBm P_{SAT}
- Gain: 34 dB
- Output TOI: 29 dBm
- Noise Figure: 3 dB
- Bias: $V_D = 5$ V, $I_D = 200$ mA, $V_{G1} = -0.7$ V, $V_{G2} = -0.6$ V Typical
- VSWR: 5 to 6
- Package Dimensions: 8.0 x 8.0 x 2.1 mm

General Description

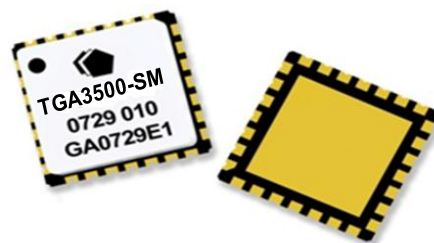
TriQuint's TGA3500-SM is a variable gain amplifier capable of supporting a variety of applications. The TGA3500-SM operates from 2 to 12 GHz and is designed using proven TriQuint's 0.15um pHEMT production process.

The TGA3500-SM typically provides 23 dBm of linear power with 34 dB of small signal gain and 29 dBm of output TOI. The Noise Figure is typically 3 dB.

The TGA3500-SM is available in a low-cost, surface mount 28 lead 8x8 AIN QFN package base with an Air cavity ceramic Lid. The TGA3500-SM is ideally suited to support both commercial and defense related applications.

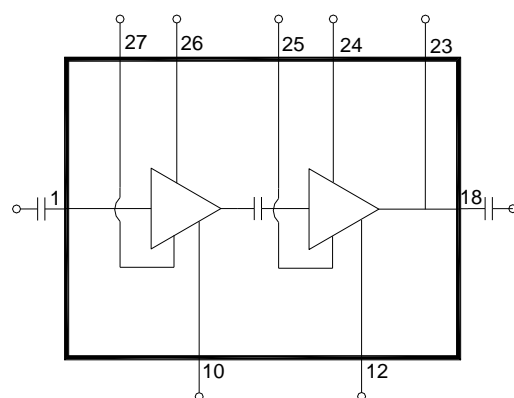
Lead-free and RoHS compliant.

Evaluation Boards are available upon request.



QFN 8x8mm 28L

Functional Block Diagram



Pad Configuration

| Pad No. | Symbol |
|-------------------------------|---------------|
| 1-4, 6-9, 11,13-17, 19-22, 28 | No Connection |
| 5 | RF IN |
| 10 | V_{G1} |
| 12 | V_{G2} |
| 18 | RF OUT |
| 23 | V_{D2T} |
| 24 | V_{D2} |
| 25 | V_{CTRL2} |
| 26 | V_{D1} |
| 27 | V_{CTRL1} |

Ordering Information

| Part | ECCN | Description |
|------------|-------|--------------------------|
| TGA3500-SM | EAR99 | 2-12 GHz Gain Driver Amp |

Absolute Maximum Ratings

| Parameter | Value |
|---|-----------------------------|
| Drain Voltage (V_{D1} , V_{D2}) | 6 V |
| Drain to Gate Voltage ($V_{D1}-V_{G1}$, $V_{D2}-V_{G2}$) | 11 V |
| Drain to Control Voltage ($V_{D1}-V_{CTRL1}$, $V_{D2}-V_{CTRL2}$) | 7 V |
| Gate Voltage Range (V_{G1} , V_{G2}) | -5 to 0 V |
| Control Voltage (V_{CTRL1} , V_{CTRL2}) | (V_D-7) to 5 V |
| Drain Current (I_{D1} , I_{D2}) | 192 mA, 192 mA |
| Gate Current (I_{G1} , I_{G2}) | -3.6 to 101 mA |
| Control Current (I_{CTRL1} , I_{CTRL2}) | -2.7 to 76 mA |
| Power Dissipation (P_{DISS}) | 3.8 W |
| RF Input Power, CW, 50 Ω , $T = 25^\circ\text{C}$ (P_{IN}) | +25 dBm |
| Channel Temperature (T_{CH}) | 200 $^\circ\text{C}$ |
| Mounting Temperature (30 Seconds) | 260 $^\circ\text{C}$ |
| Storage Temperature | -40 to 150 $^\circ\text{C}$ |

Operation of this device outside the parameter ranges given above may cause permanent damage. These are stress ratings only, and functional operation of the device at these conditions is not implied.

Recommended Operating Conditions

| Parameter | Value |
|-----------------------------------|---------------|
| Drain Voltage (V_D) | 5 V |
| Drain Current (I_{D1}) | 40 mA |
| Total Drain Current (I_{D2T}) | 200 mA |
| Gate Voltage (V_{G1}) | -0.7 V (Typ.) |
| Gate Voltage (V_{G2}) | -0.6 V (Typ.) |
| Control Voltage (V_{CTRL1}) | -0.6 V |
| Control Voltage (V_{CTRL2}) | +0.2 V |

Electrical specifications are measured at specified test conditions. Specifications are not guaranteed over all recommended operating conditions.

Electrical Specifications

Test conditions unless otherwise noted: 25 $^\circ\text{C}$, $V_D = 5$ V, $I_{D2T} = 200$ mA ($I_{D1} = 40$ mA, $I_{D2} = 160$ mA), $V_{CTRL1} = -0.6$ V, $V_{CTRL2} = +0.2$ V, $V_{G1} = -0.7$ V, $V_{G2} = -0.6$ V

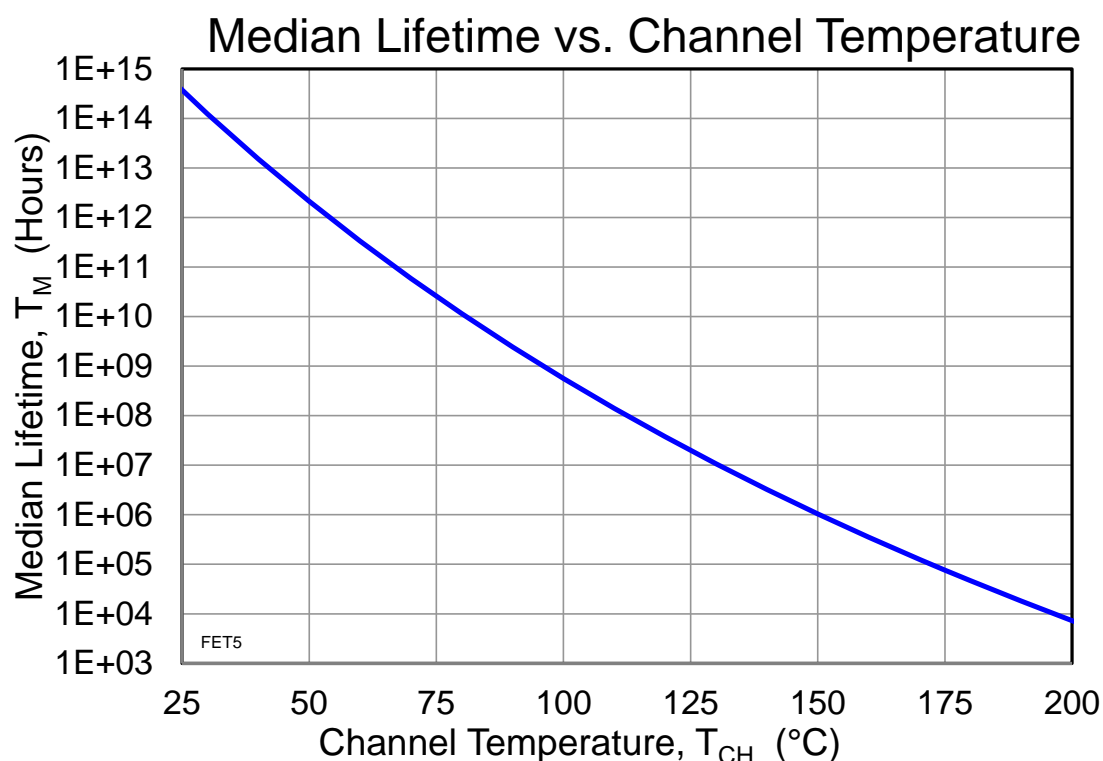
| Parameter | Min | Typical | Max | Units |
|-------------------------------|-----|---------|-----|----------------------|
| Operational Frequency Range | 2 | | 12 | GHz |
| Gain | | 34 | | dB |
| Input Return Loss | | 15 | | dB |
| Output Return Loss | | 14 | | dB |
| Output Power at Saturation | | 23 | | dBm |
| Output TOI | | 29 | | dBm |
| Noise Figure | | 3 | | dB |
| Gain Temperature Coefficient | | -0.016 | | dB/ $^\circ\text{C}$ |
| Power Temperature Coefficient | | -0.002 | | dB/ $^\circ\text{C}$ |

Thermal and Reliability Information

| Parameter | Test Conditions | Value | Units |
|--|---|-------------------|-------|
| Thermal Resistance, θ_{JC} | Tbaseplate = 85 °C | 33 | °C/W |
| Channel Temperature, T_{CH} (Without RF Drive) | Tbaseplate = 85 °C, $V_D = 5$ V, $I_{DQ} = 200$ mA, $P_{DISS} = 1$ W | 111 | °C |
| Median Lifetime, T_M (Without RF Drive) | | 1.2×10^8 | Hrs |
| Channel Temperature, T_{CH} (Under RF Drive) | Tbaseplate = 85 °C, $V_D = 5$ V, $P_{DISS} = 1$ W, $I_{DD} = 227$ mA, $P_{OUT} = 22$ dBm | 117 | °C |
| Median Lifetime, T_M (Under RF Drive) | | 5.5×10^7 | Hrs |

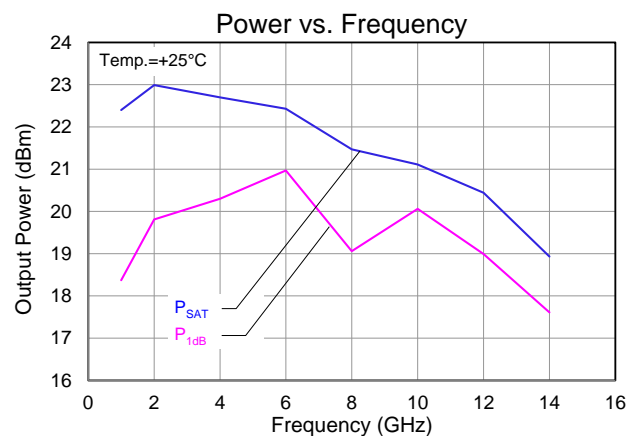
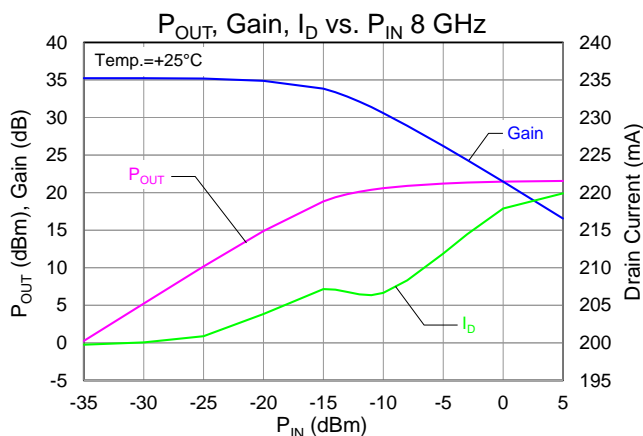
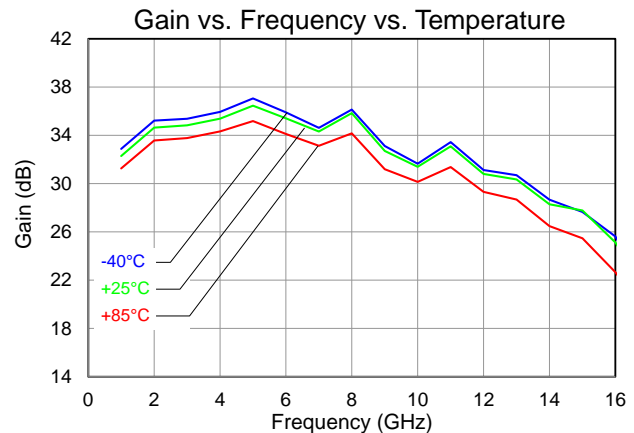
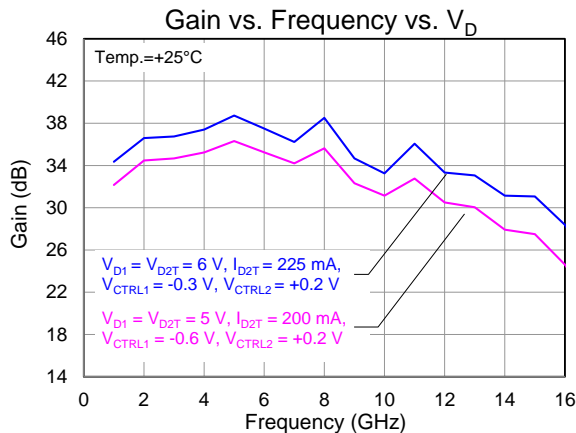
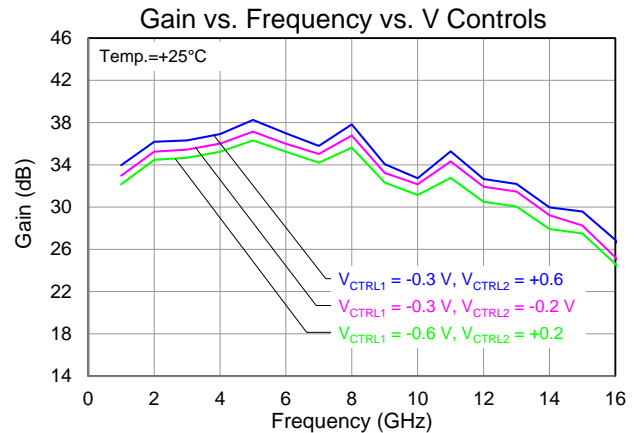
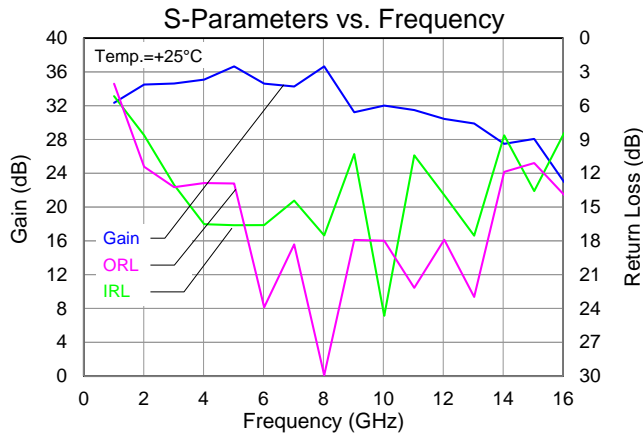
Notes: Thermal resistance measured to back of package.

Median Lifetime



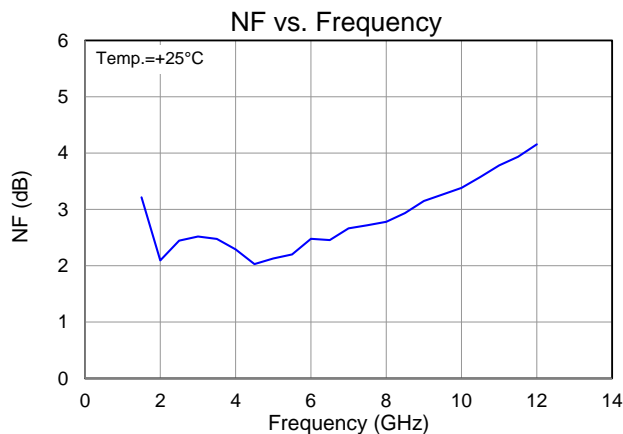
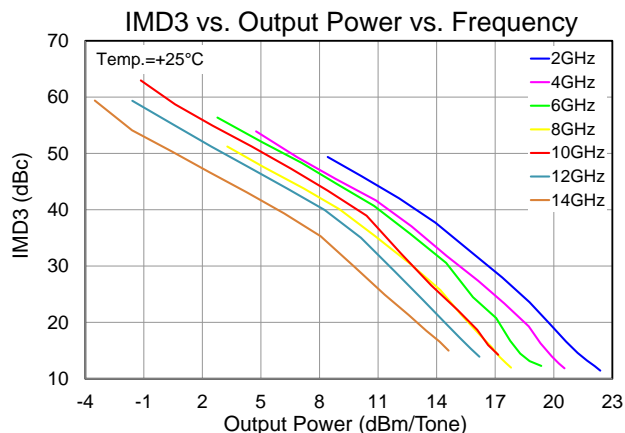
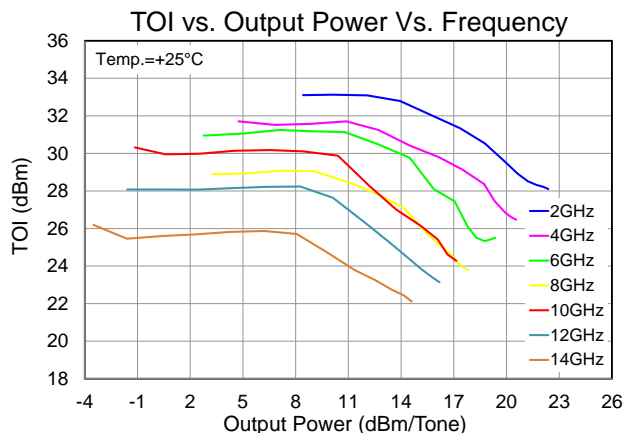
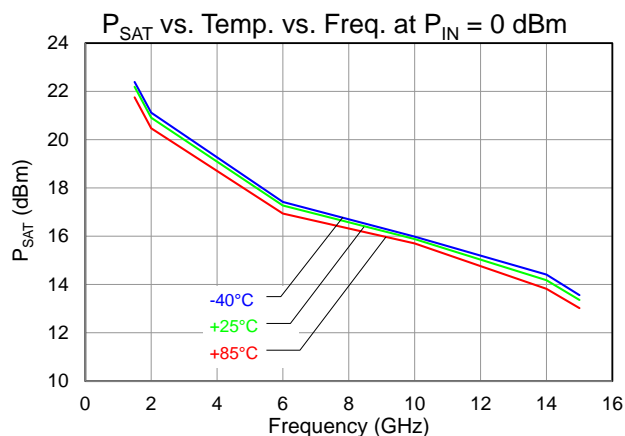
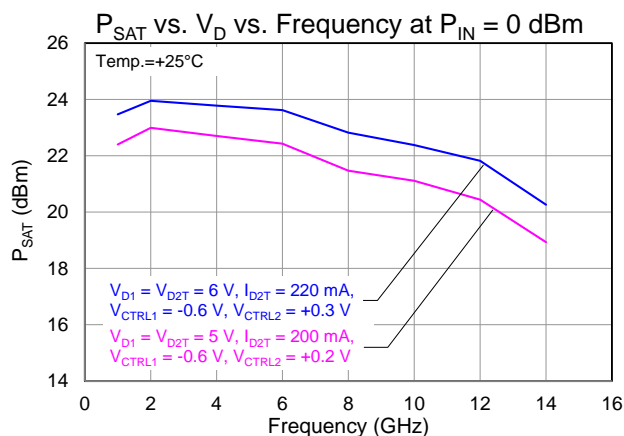
Typical Performance

Conditions unless otherwise specified: $V_{D1} = V_{D2T} = 5\text{ V}$, $I_{D1} = 40\text{ mA}$, $I_{D2T} = 200\text{ mA}$, $V_{G1} = -0.7\text{ V}$, $V_{G2} = -0.6\text{ V Typ.}$, $V_{CTRL1} = -0.6\text{ V}$, $V_{CTRL2} = +0.2\text{ V}$

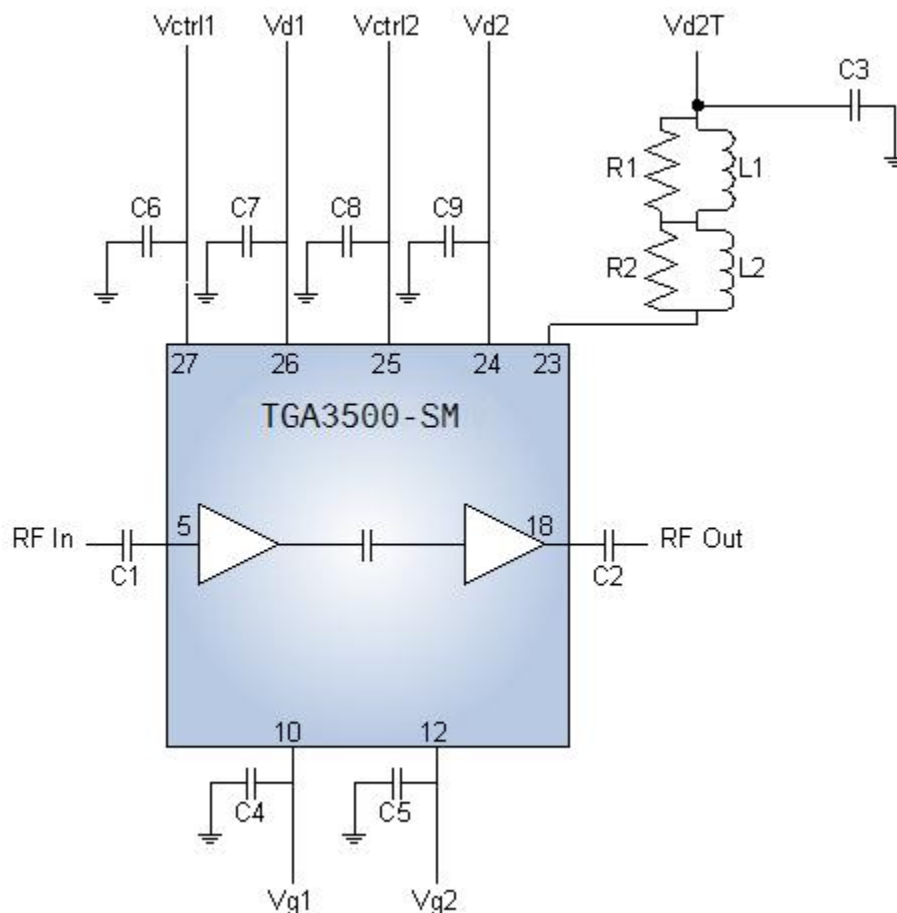


Typical Performance

Conditions unless otherwise specified: $V_{D1} = V_{D2T} = 5\text{ V}$, $I_{D1} = 40\text{ mA}$, $I_{D2T} = 200\text{ mA}$, $V_{G1} = -0.7\text{ V}$,
 $V_{G2} = -0.6\text{ V Typ.}$, $V_{CTRL1} = -0.6\text{ V}$, $V_{CTRL2} = +0.2\text{ V}$



Application Circuit



Notes: To prevent damage to the device due to overshoot or oscillation issues, we recommend that current limits for all power supplies are set properly for each power supply before applying the voltage. The following are recommended current limits for each power supply:

- Set 10 mA current limit to V_{G1} and V_{G2}
- Set 20 mA current limit to V_{CTRL1} and V_{CTRL2}
- Set 300 mA current limit to V_{D1} and V_{D2T}

Bias-up Procedure

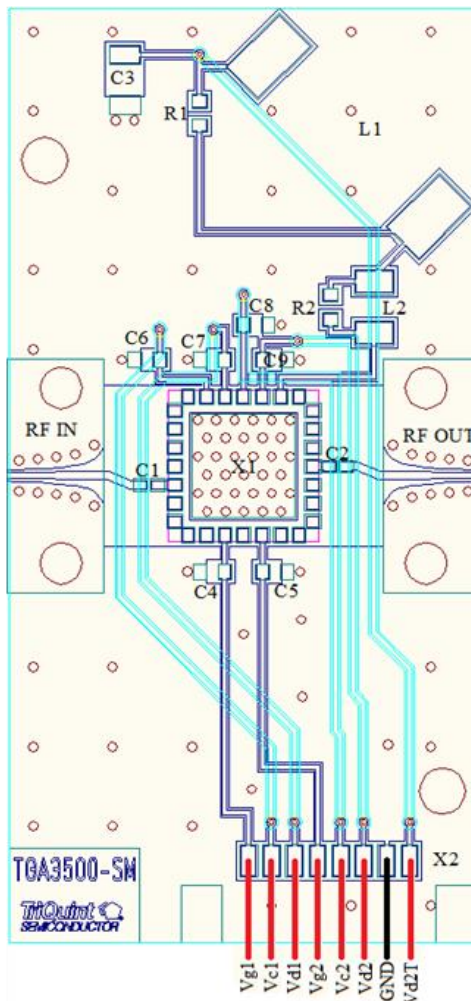
1. Apply -1.5 V V_{G1} and V_{G2} .
2. Apply -0.6 V to V_{CTRL1} .
3. Apply +0.2 V to V_{CTRL2} .
4. Apply 5 V to V_{D1} and V_{D2T} .
5. Adjust V_{G1} until $I_{D2T} = 40$ mA ($V_{G1} \sim -0.7$ V Typ.).
6. Adjust V_{G2} until $I_{D2T} = 200$ mA ($V_{G2} \sim -0.6$ V Typ.).
7. Turn on RF power.

Bias-down Procedure

1. Turn off RF supply.
2. Reduce V_{G2} and V_{G1} to -1.5 V.
3. Set V_{CTRL2} to 0 V.
4. Set V_{CTRL1} to 0 V.
5. Set V_{D1} and V_{D2T} to 0 V.
6. Set V_{G2} to 0 V.
7. Set V_{G1} to 0 V.

Recommended Board Layout Assembly

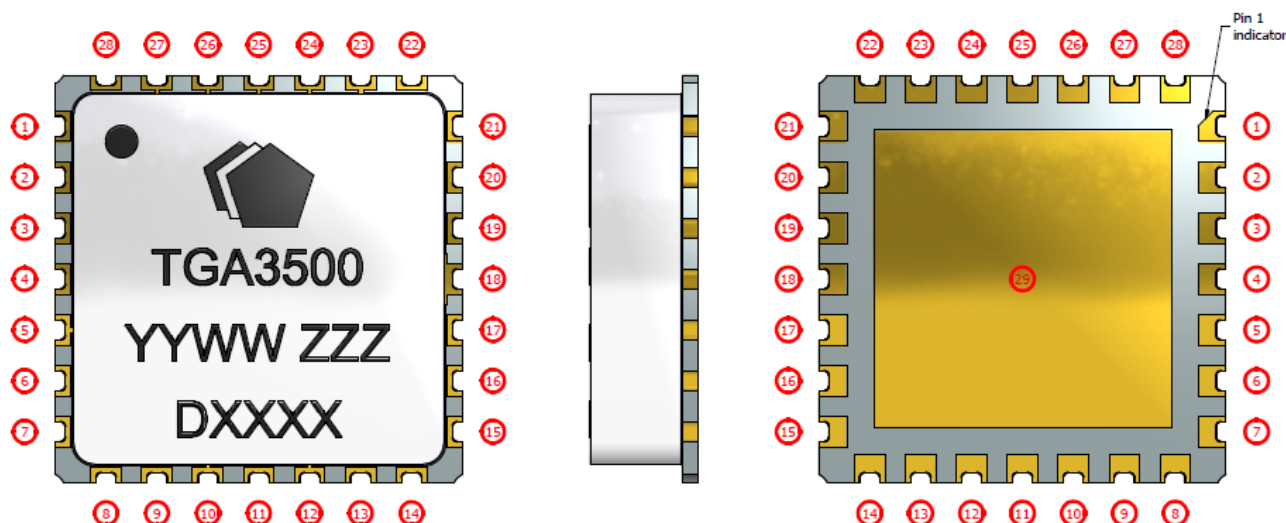
Top dielectric material is R40030 0.008 inch thickness with 0.5 oz. copper, and bottom dielectric material is FR4 0.008 inch.



Bill of Materials

| Reference Design | Value | Description | Manufacturer | Part Number |
|------------------|----------|-------------------------------|--------------|--------------------|
| L1 | 220 uH | Fixed inductor CHOKE COIL | Panasonic | ELL-CTV221M |
| L2 | 330 uH | Fixed Inductor | Panasonic | ELJ-FAR33MF2 |
| R1, R2 | 270 Ohms | Resistor, 0603 (SMD) | Panasonic | ERJ-3GEYJ271V |
| C1, C2 | 2.2 pF | Cap, 0402, 50V, 5% (SMD/SMT) | Murata | GJM1555C1H2R2WB01D |
| C3 | 10 uF | Cap, Tantalum, 16V, 10% (SMD) | AVX | TAJA106K016R |
| C4, C5, C7, C9 | 10 uF | Cap, 0603, 6.3V, 20 %, X5R | Murata | GRM188R60J106ME47D |
| C6, C8 | 0.1 uF | Cap, 0603, 16V, 20% (SMT/SMD) | AVX | 0603YG104ZAT2A |

Pin Layout



Pin Description

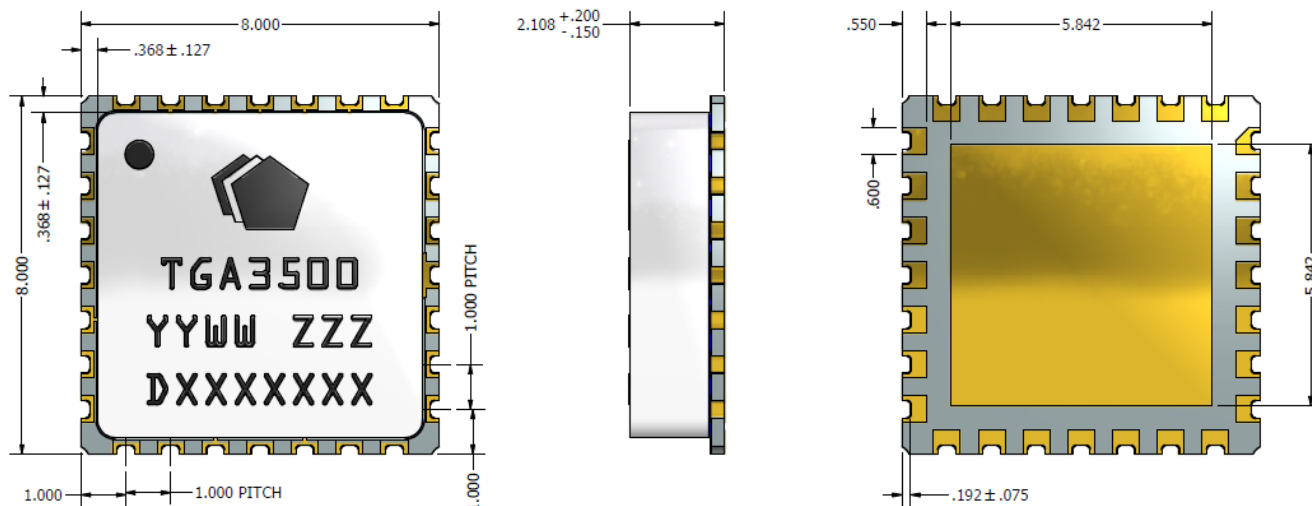
| Pin | Symbol | Description |
|-----------------------------|-------------|---|
| 1-4, 6-9, 11, 13, 19-22, 28 | N/C | No internal connection; must be grounded on PCB. |
| 5 | RF IN | RF input. |
| 10 | V_{G1} | Gate voltage. Bias network is required. ⁽¹⁾ |
| 12 | V_{G2} | Gate voltage. Bias network is required. ⁽¹⁾ |
| 18 | RF OUT | RF output. |
| 23 | V_{D2T} | Drain voltage. Bias network is required. ⁽¹⁾ |
| 24 | V_{D2} | Drain voltage. Left unconnected. |
| 25 | V_{CTRL2} | Control voltage. Bias network is required. ⁽¹⁾ |
| 26 | V_{D1} | Drain voltage. Bias network is required. ⁽¹⁾ |
| 27 | V_{CTRL1} | Control voltage. Bias network is required. ⁽¹⁾ |
| 29 | GND | Backside paddles; must be grounded on PCB. Multiple vias should be employed to minimize inductance and thermal resistance. ⁽²⁾ |

Notes:

1. See Application Circuit on page 6 as an example.
2. See Mounting Configuration on page 9 for suggested footprint.

Mechanical Information

All dimensions are in millimeters. Unless specified otherwise, tolerances: ± 0.100 mm.



Marking: Part number – TGA3500
Year/week code – YYWW
Serial No. – ZZZ
Batch ID – DXXXXX

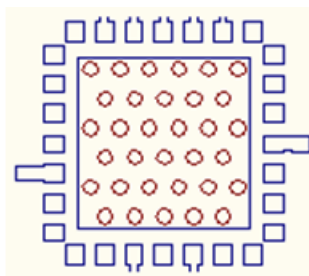
Package Materials:

Base Aluminum Nitride (AlN)
Lid White Alumina Al_2O_3

Contact Pin Plating:

Electroless Gold (Au) 0.5 – 1.0 μm
over
Electroless Nickel (Ni) 2.0 μm min.

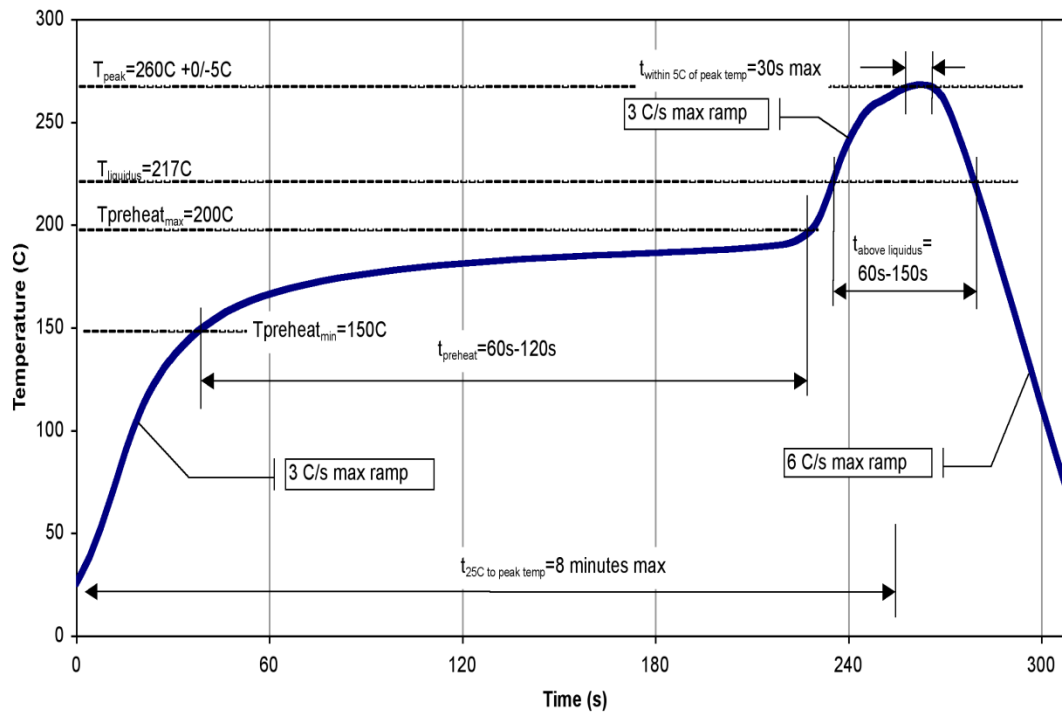
PCB Mounting Pattern



The pad pattern shown above has been developed and tested for optimized assembly at TriQuint. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.

Ground / thermal vias are critical for the proper performance of this device. Vias should use a 0.0008 in. diameter drill, and they are solid filled, copper plated shut or silver filled paste with over plating.

Recommended Soldering Temperature Profile



Product Compliance Information

ESD Sensitivity Ratings



Caution! ESD-Sensitive Device

ESD Rating: 1B
Value: (500 – 1000 V)
Test: Human Body Model (HBM)
Standard: JEDEC Standard JESD22-A114

MSL Rating

Level 1 at +260 °C convection reflow
The part is rated Moisture Sensitivity Level 1 at 260°C per JEDEC standard IPC/JEDEC J-STD-020.

ECCN

US Department of Commerce: EAR99

Solderability

Compatible with the latest version of J-STD-020, Lead free solder, 260°C

RoHS Compliance

This part is compliant with EU 2002/95/EC RoHS directive (Restrictions on the Use of Certain Hazardous Substances in Electrical and Electronic Equipment).

This product also has the following attributes:

- Lead Free
- Halogen Free (Chlorine, Bromine)
- Antimony Free
- TBBP-A (C₁₅H₁₂Br₄O₂) Free
- PFOS Free
- SVHC Free

Contact Information

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